

N-channel 25 V, 5.69 m Ω logic level MOSFET in LFPAK56 using NextPowerS3 Technology

1 April 2016

Product data sheet

1. General description

Logic level gate drive N-channel enhancement mode MOSFET in LFPAK56 package. NextPowerS3 portfolio utilising Nexperia's unique "SchottkyPlus" technology delivers high efficiency, low spiking performance usually associated with MOSFETS with an integrated Schottky or Schottky-like diode but without problematic high leakage current. NextPowerS3 is particularly suited to high efficiency applications at high switching frequencies.

2. Features and benefits

- Ultra low Q_G, Q_{GD} and Q_{OSS} for high system efficiency, especially at higher switching frequencies
- Superfast switching with soft-recovery; s-factor > 1
- Low spiking and ringing for low EMI designs
- Unique "SchottkyPlus" technology; Schottky-like performance with < 1 µA leakage at 25 °C
- Optimised for 4.5 V gate drive
- Low parasitic inductance and resistance
- High reliability clip bonded and solder die attach Power SO8 package; no glue, no wire bonds, qualified to 175 °C
- Wave solderable; exposed leads for optimal visual solder inspection

3. Applications

- On-board DC:DC solutions for server and telecommunications
- Secondary-side synchronous rectification in telecommunication applications
- Voltage regulator modules (VRM)
- Point-of-Load (POL) modules
- Power delivery for V-core, ASIC, DDR, GPU, VGA and system components
- Brushed and brushless motor control

4. Quick reference data

Table 1. Qui	ck reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	-	25	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	-	-	70	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>	-	-	47	W



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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Tj	junction temperature		-55	-	175	°C
Static chara	acteristics		1	1		
R _{DSon}	drain-source on-state resistance	V _{GS} = 4.5 V; I _D = 10 A; T _j = 25 °C; Fig. 10	-	6.8	8.35	mΩ
		V_{GS} = 10 V; I _D = 15 A; T _j = 25 °C; Fig. 10	-	4.93	5.69	mΩ
Dynamic cl	haracteristics	· · · ·	1	1		
Q _{G(tot)} total gate ch	total gate charge	I _D = 15 A; V _{DS} = 12 V; V _{GS} = 10 V; Fig. 12; Fig. 13	-	12.4	-	nC
		I_D = 15 A; V_{DS} = 12 V; V_{GS} = 4.5 V; Fig. 12; Fig. 13	-	5.7	-	nC
		$I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V$	-	6.7	-	nC
Q_{GD}	gate-drain charge	I_D = 15 A; V_{DS} = 12 V; V_{GS} = 4.5 V; Fig. 12; Fig. 13	-	1.3	-	nC
Source-dra	iin diode	, , , , , , , , , , , , , , , , , , , ,		1		
S	softness factor	I _S = 15 A; dI _S /dt = -100 A/µs; V _{GS} = 0 V; V _{DS} = 15 V; <u>Fig. 16</u>	-	1.1	-	

5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D
2	S	source		
3	S	source		G LET A
4	G	gate	ប្រុប្បូប	mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

6. Ordering information

Table 3. Ordering information							
Type number	number Package						
	Name	Description	Version				
PSMN5R4-25YLD	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669				

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7. Marking

Table 4. Marking codes	
Type number	Marking code
PSMN5R4-25YLD	5D425L

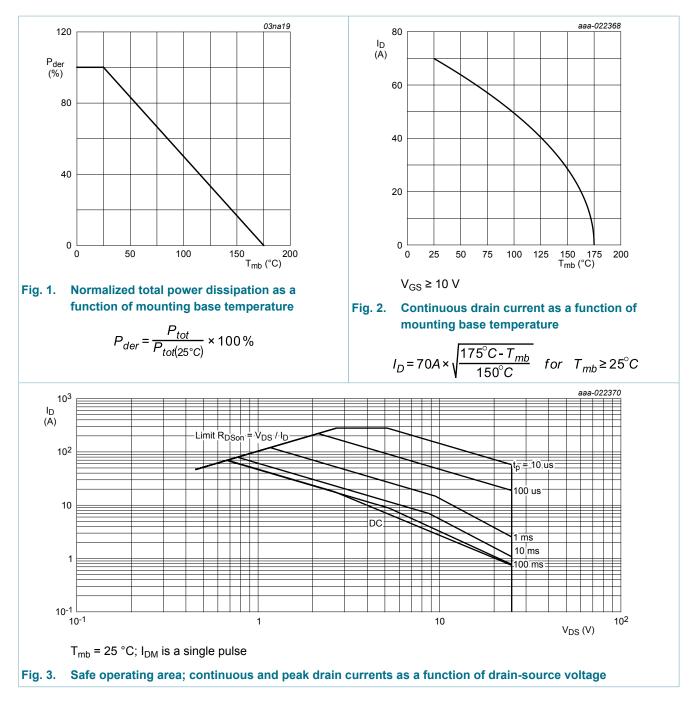
8. Limiting values

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	25	V
V _{DGR}	drain-gate voltage	25 °C ≤ T _j ≤ 175 °C; R _{GS} = 20 kΩ		-	25	V
V _{GS}	gate-source voltage			-20	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	47	W
ID	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>		-	70	Α
		V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 2</u>		-	49	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; Fig. 3		-	280	Α
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T _{sld(M)}	peak soldering temperature			-	260	°C
V _{ESD}	electrostatic discharge voltage	НВМ		300	-	V
Source-dra	in diode		1			
I _S	source current	T _{mb} = 25 °C		-	39	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$		-	280	Α
Avalanche	ruggedness	1	1			
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 15 A; $V_{sup} \le 25$ V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped; t_D = 311 μs	[1]	-	75.8	mJ

[1] Protected by 100% test

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9. Thermal characteristics

Table 6. Th	nermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	<u>Fig. 4</u>	-	2.75	3.17	K/W

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance	Fig. 5	-	50	-	K/W
	from junction to ambient	<u>Fig. 6</u>	-	125	-	K/W

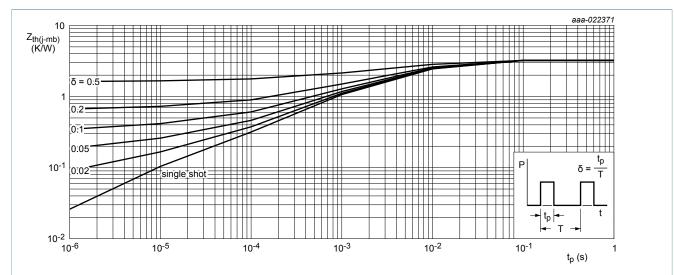
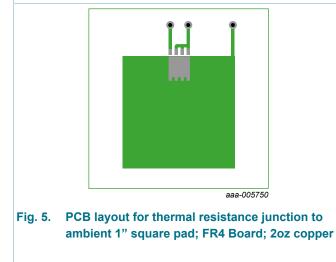


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration



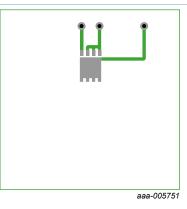


Fig. 6. PCB layout for thermal resistance junction to ambient minimum footprint; FR4 Board; 2oz copper

10. Characteristics

Table 7. C	haracteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	Static characteristics					
V _{(BR)DSS} drain-source	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	25	-	-	V	
	breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C	22.5	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = 25 \text{ °C}$	1.2	1.8	2.2	V

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$\Delta V_{GS(th)} / \Delta T$	gate-source threshold voltage variation with temperature	25 °C ≤ T _j ≤ 175 °C	-	-4.2	-	mV/K
I _{DSS}	drain leakage current	V_{DS} = 20 V; V_{GS} = 0 V; T_j = 25 °C	-	-	1	μA
		V_{DS} = 20 V; V_{GS} = 0 V; T_j = 125 °C	-	1.3	-	μA
I _{GSS}	gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
R _{DSon}	drain-source on-state resistance	V_{GS} = 4.5 V; I_D = 10 A; T_j = 25 °C; Fig. 10	-	6.8	8.35	mΩ
		V _{GS} = 4.5 V; I _D = 10 A; T _j = 175 °C; Fig. 10; Fig. 11	-	-	14.2	mΩ
		V _{GS} = 10 V; I _D = 15 A; T _j = 25 °C; <u>Fig. 10</u>	-	4.93	5.69	mΩ
		V _{GS} = 10 V; I _D = 15 A; T _j = 175 °C; <u>Fig. 10; Fig. 11</u>	-	-	9.67	mΩ
R _G	gate resistance	f = 1 MHz	-	0.75	-	Ω
Dynamic ch	aracteristics					
Q _{G(tot)}	total gate charge	I _D = 15 A; V _{DS} = 12 V; V _{GS} = 10 V; Fig. 12; Fig. 13	-	12.4	-	nC
		I _D = 15 A; V _{DS} = 12 V; V _{GS} = 4.5 V; Fig. 12; Fig. 13	-	5.7	-	nC
		I _D = 0 A; V _{DS} = 0 V; V _{GS} = 10 V	-	6.7	-	nC
Q _{GS}	gate-source charge	I_D = 15 A; V_{DS} = 12 V; V_{GS} = 4.5 V; Fig. 12; Fig. 13	-	2.5	-	nC
Q _{GS(th)}	pre-threshold gate- source charge	I_D = 10 A; V_{DS} = 12 V; V_{GS} = 4.5 V; Fig. 12; Fig. 13	-	1.4	-	nC
$Q_{GS(th-pl)}$	post-threshold gate- source charge	I _D = 15 A; V _{DS} = 12 V; V _{GS} = 4.5 V; Fig. 12; Fig. 13	-	1.1	-	nC
Q _{GD}	gate-drain charge		-	1.3	-	nC
V _{GS(pl)}	gate-source plateau voltage	I _D = 15 A; V _{DS} = 12 V; <u>Fig. 12</u> ; <u>Fig. 13</u>	-	2.9	-	V
C _{iss}	input capacitance	V_{DS} = 12 V; V_{GS} = 0 V; f = 1 MHz;	-	858	-	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 14</u>	-	626	-	pF
C _{rss}	reverse transfer capacitance		-	53	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 12 V; R _L = 1 Ω; V _{GS} = 4.5 V;	-	8.4	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega$	-	7.8	-	ns
t _{d(off)}	turn-off delay time	1	-	8.7	-	ns
t _f	fall time		-	4.9	-	ns

PSMN5R4-25YLD

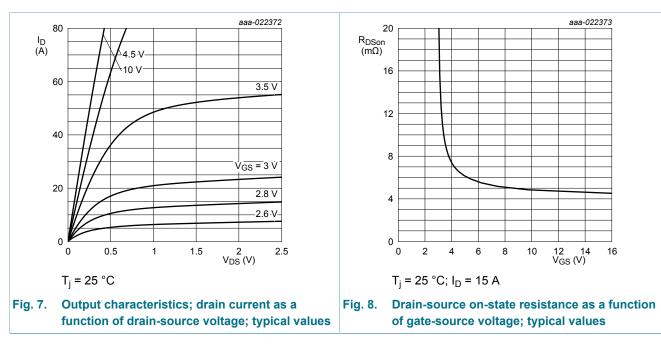
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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Q _{oss}	output charge	V _{GS} = 0 V; V _{DS} = 12 V; f = 1 MHz; T _j = 25 °C		-	9.7	-	nC
Source-dra	in diode						
V _{SD}	source-drain voltage	I_{S} = 10 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 15</u>		-	0.81	1.2	V
t _{rr}	reverse recovery time	I_{S} = 15 A; dI_{S}/dt = -100 A/µs; V_{GS} = 0 V;		-	22.7	-	ns
Q _r	recovered charge	V _{DS} = 15 V; <u>Fig. 16</u>	[1]	-	12.9	-	nC
t _a	reverse recovery rise time			-	10.6	-	ns
t _b	reverse recovery fall time			-	12.1	-	ns
S	softness factor			-	1.1	-	

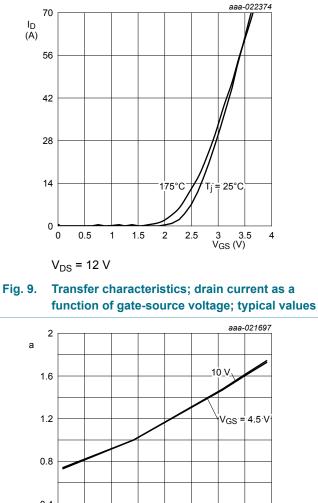


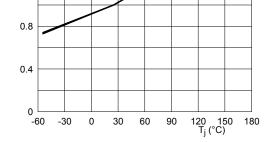
[1] includes capacitive recovery

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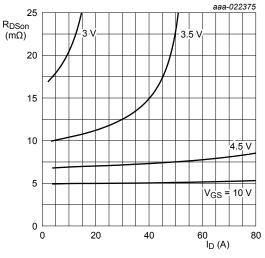
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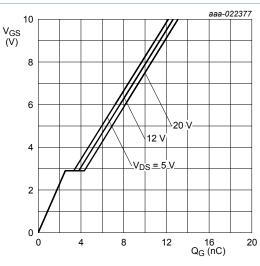












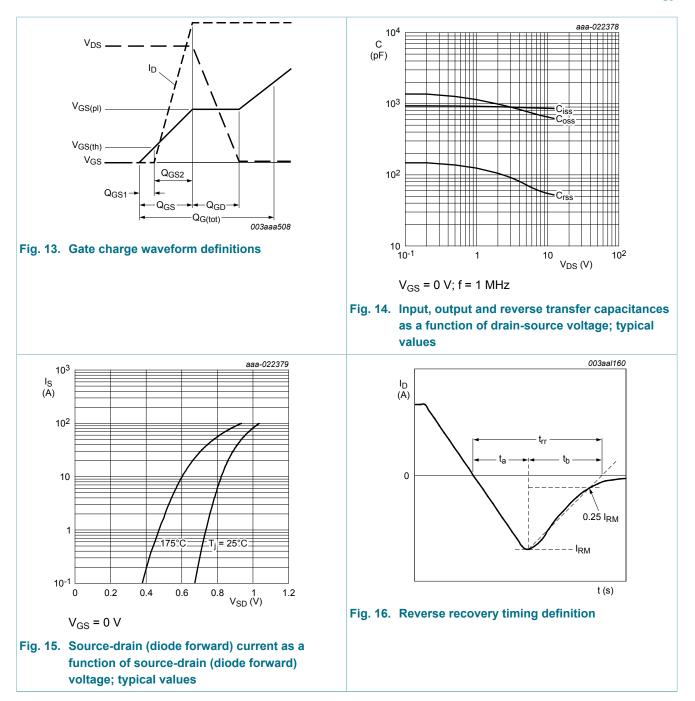
V_{GS} = 0 V; f = 1 MHz



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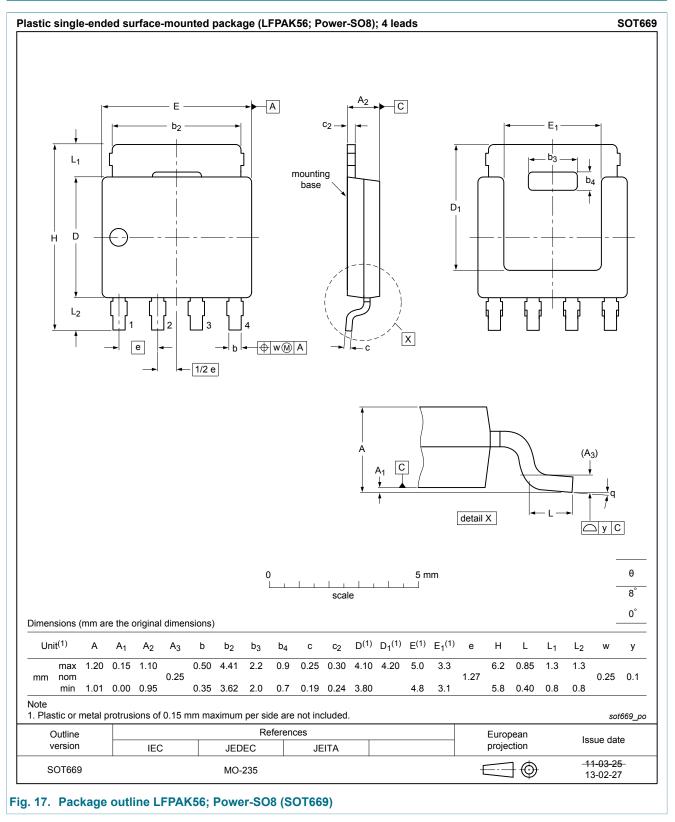
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11. Package outline



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12. Legal information

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